

# MA2C188

## Silicon epitaxial planar type

For high speed and high voltage switching, small-power rectification

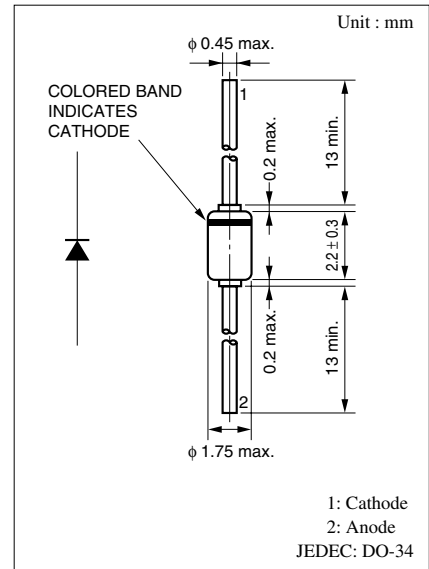
### ■ Features

- Small glass type (DO-34) package, allowing to insert into a 5 mm pitch hole
- High voltage ( $V_R$ : 200 V) rectification is possible

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Peak reverse voltage	$V_{RM}$	250	V
Average power dissipation	$P_{F(AV)}$	400	mW
Output current	$I_O$	200	mA
Repetitive peak forward current	$I_{FRM}$	625	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$

Note) \* :  $t = 1 \text{ s}$



1: Cathode  
2: Anode  
JEDEC: DO-34

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200 \text{ V}$			200	nA
Forward voltage (DC)	$V_F$	$I_F = 200 \text{ mA}$			1.2	V
Reverse voltage (DC)	$V_R$	$I_R = 100 \mu\text{A}$	250			V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		1.0		pF
Reverse recovery time*	$t_{rr}$	$I_F = 10 \text{ mA}, V_R = 1 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			60	ns

Note) 1. Rated input/output frequency: 20 MHz

2. \* :  $t_{rr}$  measuring circuit

